Lattice Semiconductor Corporation - LCMXO2-1200ZE-1UWG25ITR Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	160
Number of Logic Elements/Cells	1280
Total RAM Bits	65536
Number of I/O	18
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	25-UFBGA, WLCSP
Supplier Device Package	25-WLCSP
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo2-1200ze-1uwg25itr

MachXO2 Family Data Sheet Introduction

May 2016 Data Sheet DS1035

Features

- **Flexible Logic Architecture**
  - Six devices with 256 to 6864 LUT4s and 18 to 334 I/Os
- **Ultra Low Power Devices**
  - Advanced 65 nm low power process
  - As low as 22 µW standby power
  - Programmable low swing differential I/Os
  - Stand-by mode and other power saving options
- **Embedded and Distributed Memory**
  - Up to 240 kbits sysMEM™ Embedded Block RAM
  - Up to 54 kbits Distributed RAM
  - Dedicated FIFO control logic
- **On-Chip User Flash Memory**
  - Up to 256 kbits of User Flash Memory
  - 100,000 write cycles
  - Accessible through WISHBONE, SPI, I^2C and JTAG interfaces
  - Can be used as soft processor PROM or as Flash memory
- **Pre-Engineered Source Synchronous I/O**
  - DDR registers in I/O cells
  - Dedicated gearing logic
  - 7:1 Gearing for Display I/Os
  - Generic DDR, DDRX2, DDRX4
  - Dedicated DDR/DDR2/LPDDR memory with DQS support
- **High Performance, Flexible I/O Buffer**
  - Programmable sysIO™ buffer supports wide range of interfaces:
    - LVCMOS 3.3/2.5/1.8/1.5/1.2
    - LVTTL
    - PCI
    - LVDS, Bus-LVDS, MLVDS, RSDS, LVPECL
    - SSTL 25/18
    - HSTL 18
    - Schmitt trigger inputs, up to 0.5 V hysteresis
  - I/Os support hot socketing
  - On-chip differential termination
  - Programmable pull-up or pull-down mode
- **Flexible On-Chip Clocking**
  - Eight primary clocks
  - Up to two edge clocks for high-speed I/O interfaces (top and bottom sides only)
  - Up to two analog PLLs per device with fractional-n frequency synthesis
    - Wide input frequency range (7 MHz to 400 MHz)
- **Non-volatile, Infinitely Reconfigurable**
  - Instant-on – powers up in microseconds
  - Single-chip, secure solution
  - Programmable through JTAG, SPI or I^2C
  - Supports background programming of non-volatile memory
  - Optional dual boot with external SPI memory
- **TransFR™ Reconfiguration**
  - In-field logic update while system operates
- **Enhanced System Level Support**
  - On-chip hardened functions: SPI, I^2C, timer/counter
  - On-chip oscillator with 5.5% accuracy
  - Unique TraceID for system tracking
  - One Time Programmable (OTP) mode
  - Single power supply with extended operating range
  - IEEE Standard 1149.1 boundary scan
  - IEEE 1532 compliant in-system programming
- **Broad Range of Package Options**
  - TQFP, WLCSP, ucBGA, csBGA, caBGA, ftBGA, fpBGA, QFN package options
  - Small footprint package options
    - As small as 2.5 mm x 2.5 mm
  - Density migration supported
  - Advanced halogen-free packaging

Table 1-1. MachXO2™ Family Selection Guide

		XO2-256	XO2-640	XO2-640U[1]	XO2-1200	XO2-1200U[1]	XO2-2000	XO2-2000U[1]	XO2-4000	XO2-7000
LUTs		256	640	640	1280	1280	2112	2112	4320	6864
Distributed RAM (kbits)		2	5	5	10	10	16	16	34	54
EBR SRAM (kbits)		0	18	64	64	74	74	92	92	240
Number of EBR SRAM Blocks (9 kbits/block)		0	2	7	7	8	8	10	10	26
UFM (kbits)		0	24	64	64	80	80	96	96	256
Device Options:	HC[2]	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes
	HE[3]						Yes	Yes	Yes	Yes
	ZE[4]	Yes	Yes		Yes		Yes		Yes	Yes
Number of PLLs		0	0	1	1	1	1	2	2	2
Hardened Functions:	I2C	2	2	2	2	2	2	2	2	2
	SPI	1	1	1	1	1	1	1	1	1
	Timer/Counter	1	1	1	1	1	1	1	1	1
Packages						**IO**				
25-ball WLCSP[5] (2.5 mm x 2.5 mm, 0.4 mm)					18					
32 QFN[6] (5 mm x 5 mm, 0.5 mm)		21			21					
48 QFN[8, 9] (7 mm x 7 mm, 0.5 mm)		40	40							
49-ball WLCSP[5] (3.2 mm x 3.2 mm, 0.4 mm)							38			
64-ball ucBGA (4 mm x 4 mm, 0.4 mm)		44								
84 QFN[7] (7 mm x 7 mm, 0.5 mm)									68	
100-pin TQFP (14 mm x 14 mm)		55	78		79		79			
132-ball csBGA (8 mm x 8 mm, 0.5 mm)		55	79		104		104		104	
144-pin TQFP (20 mm x 20 mm)				107	107		111		114	114
184-ball csBGA[7] (8 mm x 8 mm, 0.5 mm)									150	
256-ball caBGA (14 mm x 14 mm, 0.8 mm)							206		206	206
256-ball ftBGA (17 mm x 17 mm, 1.0 mm)						206	206		206	206
332-ball caBGA (17 mm x 17 mm, 0.8 mm)									274	278
484-ball ftBGA (23 mm x 23 mm, 1.0 mm)								278	278	334

1. Ultra high I/O device.
2. High performance with regulator – VCC = 2.5 V, 3.3 V
3. High performance without regulator – V_{CC} = 1.2 V
4. Low power without regulator – V_{CC} = 1.2 V
5. WLCSP package only available for ZE devices.
6. 32 QFN package only available for HC and ZE devices.
7. 184 csBGA package only available for HE devices.
8. 48-pin QFN information is ‘Advanced’.
9. 48 QFN package only available for HC devices.

The logic blocks, Programmable Functional Unit (PFU) and sysMEM EBR blocks, are arranged in a two-dimensional grid with rows and columns. Each row has either the logic blocks or the EBR blocks. The PIO cells are located at the periphery of the device, arranged in banks. The PFU contains the building blocks for logic, arithmetic, RAM, ROM, and register functions. The PIOs utilize a flexible I/O buffer referred to as a sysIO buffer that supports operation with a variety of interface standards. The blocks are connected with many vertical and horizontal routing channel resources. The place and route software tool automatically allocates these routing resources.

In the MachXO2 family, the number of sysIO banks varies by device. There are different types of I/O buffers on the different banks. Refer to the details in later sections of this document. The sysMEM EBRs are large, dedicated fast memory blocks; these blocks are found in MachXO2-640/U and larger devices. These blocks can be configured as RAM, ROM or FIFO. FIFO support includes dedicated FIFO pointer and flag “hard” control logic to minimize LUT usage.

The MachXO2 registers in PFU and sysI/O can be configured to be SET or RESET. After power up and device is configured, the device enters into user mode with these registers SET/RESET according to the configuration setting, allowing device entering to a known state for predictable system function.

The MachXO2 architecture also provides up to two sysCLOCK Phase Locked Loop (PLL) blocks on MachXO2-640U, MachXO2-1200/U and larger devices. These blocks are located at the ends of the on-chip Flash block. The PLLs have multiply, divide, and phase shifting capabilities that are used to manage the frequency and phase relationships of the clocks.

MachXO2 devices provide commonly used hardened functions such as SPI controller, I^2C controller and timer/counter. MachXO2-640/U and higher density devices also provide User Flash Memory (UFM). These hardened functions and the UFM interface to the core logic and routing through a WISHBONE interface. The UFM can also be accessed through the SPI, I^2C and JTAG ports.

Every device in the family has a JTAG port that supports programming and configuration of the device as well as access to the user logic. The MachXO2 devices are available for operation from 3.3 V, 2.5 V and 1.2 V power supplies, providing easy integration into the overall system.

PFU Blocks

The core of the MachXO2 device consists of PFU blocks, which can be programmed to perform logic, arithmetic, distributed RAM and distributed ROM functions. Each PFU block consists of four interconnected slices numbered 0 to 3 as shown in Figure 2-3. Each slice contains two LUTs and two registers. There are 53 inputs and 25 outputs associated with each PFU block.

Table 2-5. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
True Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
Pseudo Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18
FIFO	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18

Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration. EBR initialization data can be loaded from the UFM. To maximize the number of UFM bits, initialize the EBRs used in your design to an all-zero pattern. Initializing to an all-zero pattern does not use up UFM bits. MachXO2 devices have been designed such that multiple EBRs share the same initialization memory space if they are initialized to the same pattern.

By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

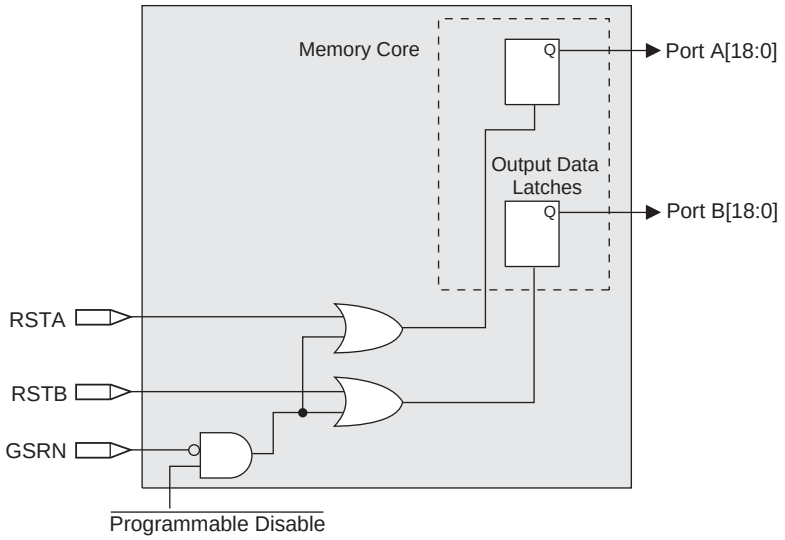
Memory Cascading

Larger and deeper blocks of RAM can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

Single, Dual, Pseudo-Dual Port and FIFO Modes

Figure 2-8 shows the five basic memory configurations and their input/output names. In all the sysMEM RAM modes, the input data and addresses for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the memory array output.

Figure 2-9. Memory Core Reset

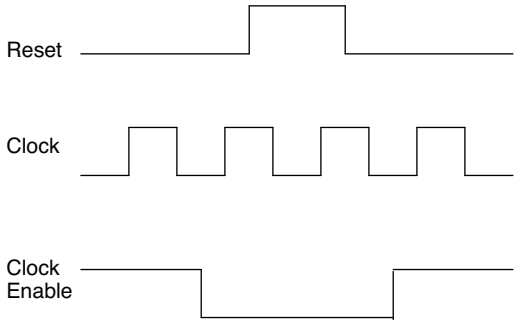


For further information on the sysMEM EBR block, please refer to TN1201, Memory Usage Guide for MachXO2 Devices.

EBR Asynchronous Reset

EBR asynchronous reset or GSR (if used) can only be applied if all clock enables are low for a clock cycle before the reset is applied and released a clock cycle after the reset is released, as shown in Figure 2-10. The GSR input to the EBR is always asynchronous.

Figure 2-10. EBR Asynchronous Reset (Including GSR) Timing Diagram



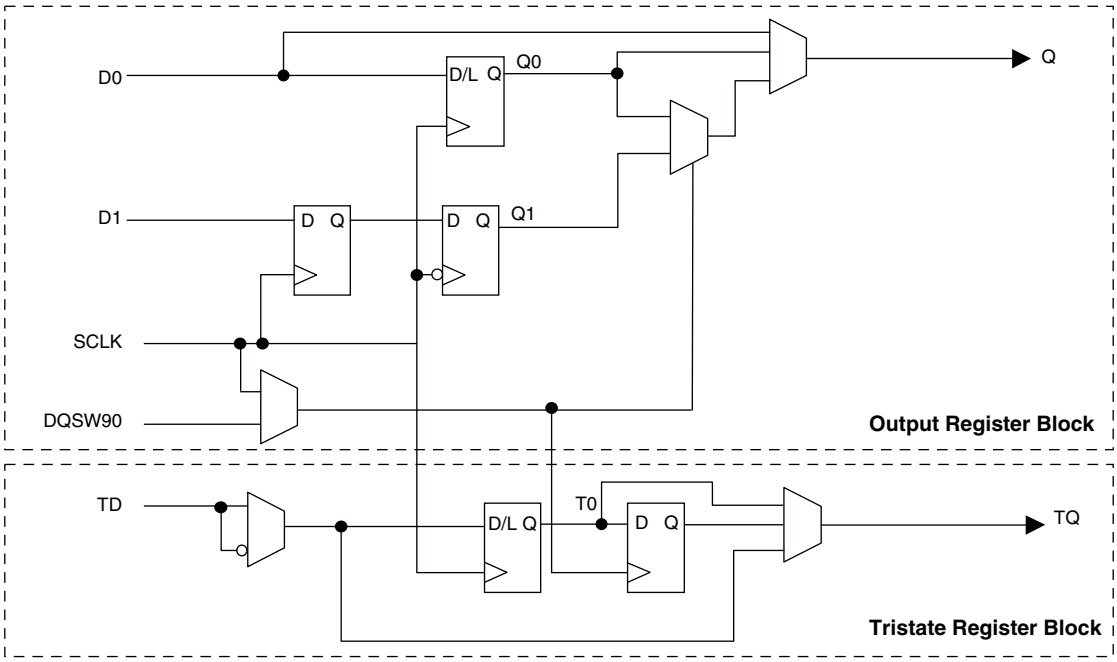
If all clock enables remain enabled, the EBR asynchronous reset or GSR may only be applied and released after the EBR read and write clock inputs are in a steady state condition for a minimum of $1/f_{MAX}$ (EBR clock). The reset release must adhere to the EBR synchronous reset setup time before the next active read or write clock edge.

If an EBR is pre-loaded during configuration, the GSR input must be disabled or the release of the GSR during device wake up must occur before the release of the device I/Os becoming active.

These instructions apply to all EBR RAM, ROM and FIFO implementations. For the EBR FIFO mode, the GSR signal is always enabled and the WE and RE signals act like the clock enable signals in Figure 2-10. The reset timing rules apply to the RPReset input versus the RE input and the RST input versus the WE and RE inputs. Both RST and RPReset are always asynchronous EBR inputs. For more details refer to TN1201, Memory Usage Guide for MachXO2 Devices.

Note that there are no reset restrictions if the EBR synchronous reset is used and the EBR GSR input is disabled.

Figure 2-15. MachXO2 Output Register Block Diagram (PIO on the Right Edges)



Tri-state Register Block

The tri-state register block registers tri-state control signals from the core of the device before they are passed to the sysIO buffers. The block contains a register for SDR operation. In SDR, TD input feeds one of the flip-flops that then feeds the output.

The tri-state register blocks on the right edge contain an additional register for DDR memory operation. In DDR memory mode, the register TS input is fed into another register that is clocked using the DQSW90 signal. The output of this register is used as a tri-state control.

Input Gearbox

Each PIC on the bottom edge has a built-in 1:8 input gearbox. Each of these input gearboxes may be programmed as a 1:7 de-serializer or as one IDDRX4 (1:8) gearbox or as two IDDRX2 (1:4) gearboxes. Table 2-9 shows the gearbox signals.

Table 2-9. Input Gearbox Signal List

Name	I/O Type	Description
D	Input	High-speed data input after programmable delay in PIO A input register block
ALIGNWD	Input	Data alignment signal from device core
SCLK	Input	Slow-speed system clock
ECLK[1:0]	Input	High-speed edge clock
RST	Input	Reset
Q[7:0]	Output	Low-speed data to device core: Video RX(1:7): Q[6:0] GDDRX4(1:8): Q[7:0] GDDRX2(1:4)(IOL-A): Q4, Q5, Q6, Q7 GDDRX2(1:4)(IOL-C): Q0, Q1, Q2, Q3

Table 2-11. I/O Support Device by Device

	MachXO2-256, MachXO2-640	MachXO2-640U, MachXO2-1200	MachXO2-1200U MachXO2-2000/U, MachXO2-4000, MachXO2-7000
Number of I/O Banks	4	4	6
Type of Input Buffers	Single-ended (all I/O banks) Differential Receivers (all I/O banks)	Single-ended (all I/O banks) Differential Receivers (all I/O banks) Differential input termination (bottom side)	Single-ended (all I/O banks) Differential Receivers (all I/O banks) Differential input termination (bottom side)
Types of Output Buffers	Single-ended buffers with complementary outputs (all I/O banks)	Single-ended buffers with complementary outputs (all I/O banks) Differential buffers with true LVDS outputs (50% on top side)	Single-ended buffers with complementary outputs (all I/O banks) Differential buffers with true LVDS outputs (50% on top side)
Differential Output Emulation Capability	All I/O banks	All I/O banks	All I/O banks
PCI Clamp Support	No	Clamp on bottom side only	Clamp on bottom side only

Table 2-12. Supported Input Standards

	VCCIO (Typ.)				
Input Standard	**3.3 V**	**2.5 V**	**1.8 V**	**1.5**	**1.2 V**
Single-Ended Interfaces					
LVTTL	✓	✓[2]	✓[2]	✓[2]	
LVCMOS33	✓	✓[2]	✓[2]	✓[2]	
LVCMOS25	✓[2]	✓	✓[2]	✓[2]	
LVCMOS18	✓[2]	✓[2]	✓	✓[2]	
LVCMOS15	✓[2]	✓[2]	✓[2]	✓	✓[2]
LVCMOS12	✓[2]	✓[2]	✓[2]	✓[2]	✓
PCI[1]	✓				
SSTL18 (Class I, Class II)	✓	✓	✓		
SSTL25 (Class I, Class II)	✓	✓			
HSTL18 (Class I, Class II)	✓	✓	✓		
Differential Interfaces					
LVDS	✓	✓			
BLVDS, MVDS, LVPECL, RSDS	✓	✓			
MIPI[3]	✓	✓			
Differential SSTL18 Class I, II	✓	✓	✓		
Differential SSTL25 Class I, II	✓	✓			
Differential HSTL18 Class I, II	✓	✓	✓		

1. Bottom banks of MachXO2-640U, MachXO2-1200/U and higher density devices only.
2. Reduced functionality. Refer to TN1202, MachXO2 sysIO Usage Guide for more detail.
3. These interfaces can be emulated with external resistors in all devices.

For more details on these embedded functions, please refer to TN1205, Using User Flash Memory and Hardened Control Functions in MachXO2 Devices.

User Flash Memory (UFM)

MachXO2-640/U and higher density devices provide a User Flash Memory block, which can be used for a variety of applications including storing a portion of the configuration image, initializing EBRs, to store PROM data or, as a general purpose user Flash memory. The UFM block connects to the device core through the embedded function block WISHBONE interface. Users can also access the UFM block through the JTAG, I^2C and SPI interfaces of the device. The UFM block offers the following features:

- Non-volatile storage up to 256 kbits
- 100K write cycles
- Write access is performed page-wise; each page has 128 bits (16 bytes)
- Auto-increment addressing
- WISHBONE interface

For more information on the UFM, please refer to TN1205, Using User Flash Memory and Hardened Control Functions in MachXO2 Devices.

Standby Mode and Power Saving Options

MachXO2 devices are available in three options for maximum flexibility: ZE, HC and HE devices. The ZE devices have ultra low static and dynamic power consumption. These devices use a 1.2 V core voltage that further reduces power consumption. The HC and HE devices are designed to provide high performance. The HC devices have a built-in voltage regulator to allow for 2.5 V V_{CC} and 3.3 V V_{CC} while the HE devices operate at 1.2 V V_{CC}.

MachXO2 devices have been designed with features that allow users to meet the static and dynamic power requirements of their applications by controlling various device subsystems such as the bandgap, power-on-reset circuitry, I/O bank controllers, power guard, on-chip oscillator, PLLs, etc. In order to maximize power savings, MachXO2 devices support an ultra low power Stand-by mode. While most of these features are available in all three device types, these features are mainly intended for use with MachXO2 ZE devices to manage power consumption.

In the stand-by mode the MachXO2 devices are powered on and configured. Internal logic, I/Os and memories are switched on and remain operational, as the user logic waits for an external input. The device enters this mode when the standby input of the standby controller is toggled or when an appropriate I^2C or JTAG instruction is issued by an external master. Various subsystems in the device such as the band gap, power-on-reset circuitry etc can be configured such that they are automatically turned “off” or go into a low power consumption state to save power when the device enters this state. Note that the MachXO2 devices are powered on when in standby mode and all power supplies should remain in the Recommended Operating Conditions.

Table 2-18. MachXO2 Power Saving Features Description

Device Subsystem	Feature Description
Bandgap	The bandgap can be turned off in standby mode. When the Bandgap is turned off, analog circuitry such as the POR, PLLs, on-chip oscillator, and referenced and differential I/O buffers are also turned off. Bandgap can only be turned off for 1.2 V devices.
Power-On-Reset (POR)	The POR can be turned off in standby mode. This monitors VCC levels. In the event of unsafe V_{CC} drops, this circuit reconfigures the device. When the POR circuitry is turned off, limited power detector circuitry is still active. This option is only recommended for applications in which the power supply rails are reliable.
On-Chip Oscillator	The on-chip oscillator has two power saving features. It may be switched off if it is not needed in your design. It can also be turned off in Standby mode.
PLL	Similar to the on-chip oscillator, the PLL also has two power saving features. It can be statically switched off if it is not needed in a design. It can also be turned off in Standby mode. The PLL will wait until all output clocks from the PLL are driven low before powering off.
I/O Bank Controller	Referenced and differential I/O buffers (used to implement standards such as HSTL, SSTL and LVDS) consume more than ratioed single-ended I/Os such as LVCMOS and LVTTL. The I/O bank controller allows the user to turn these I/Os off dynamically on a per bank selection.
Dynamic Clock Enable for Primary Clock Nets	Each primary clock net can be dynamically disabled to save power.
Power Guard	Power Guard is a feature implemented in input buffers. This feature allows users to switch off the input buffer when it is not needed. This feature can be used in both clock and data paths. Its biggest impact is that in the standby mode it can be used to switch off clock inputs that are distributed using general routing resources.

For more details on the standby mode refer to TN1198, Power Estimation and Management for MachXO2 Devices.

Power On Reset

MachXO2 devices have power-on reset circuitry to monitor V_{CCINT} and V_{CCIO} voltage levels during power-up and operation. At power-up, the POR circuitry monitors V_{CCINT} and V_{CCIO0} (controls configuration) voltage levels. It then triggers download from the on-chip configuration Flash memory after reaching the V_{PORUP} level specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. For devices without voltage regulators (ZE and HE devices), V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators (HC devices), V_{CCINT} is regulated from the V_{CC} supply voltage. From this voltage reference, the time taken for configuration and entry into user mode is specified as Flash Download Time ($t_{REFRESH}$) in the DC and Switching Characteristics section of this data sheet. Before and during configuration, the I/Os are held in tri-state. I/Os are released to user functionality once the device has finished configuration. Note that for HC devices, a separate POR circuit monitors external V_{CC} voltage in addition to the POR circuit that monitors the internal post-regulated power supply voltage level.

Once the device enters into user mode, the POR circuitry can optionally continue to monitor V_{CCINT} levels. If V_{CCINT} drops below $V_{PORDNBG}$ level (with the bandgap circuitry switched on) or below $V_{PORDNSRAM}$ level (with the bandgap circuitry switched off to conserve power) device functionality cannot be guaranteed. In such a situation the POR issues a reset and begins monitoring the V_{CCINT} and V_{CCIO} voltage levels. $V_{PORDNBG}$ and $V_{PORDNSRAM}$ are both specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet.

Note that once a ZE or HE device enters user mode, users can switch off the bandgap to conserve power. When the bandgap circuitry is switched off, the POR circuitry also shuts down. The device is designed such that a minimal, low power POR circuit is still operational (this corresponds to the $V_{PORDNSRAM}$ reset point described in the paragraph above). However this circuit is not as accurate as the one that operates when the bandgap is switched on. The low power POR circuit emulates an SRAM cell and is biased to trip before the vast majority of SRAM cells flip. If users are concerned about the V_{CC} supply dropping below V_{CC} (min) they should not shut down the bandgap or POR circuit.

Programming and Erase Flash Supply Current – ZE Devices[1, 2, 3, 4]

Symbol	Parameter	Device	Typ.[5]	Units
I_{CC}	Core Power Supply	LCMXO2-256ZE	13	mA
		LCMXO2-640ZE	14	mA
		LCMXO2-1200ZE	15	mA
		LCMXO2-2000ZE	17	mA
		LCMXO2-4000ZE	18	mA
		LCMXO2-7000ZE	20	mA
I_{CCIO}	Bank Power Supply[6]	All devices	0	mA

1. For further information on supply current, please refer to TN1198, Power Estimation and Management for MachXO2 Devices.
2. Assumes all inputs are held at V_{CCIO} or GND and all outputs are tri-stated.
3. Typical user pattern.
4. JTAG programming is at 25 MHz.
5. TJ = 25 °C, power supplies at nominal voltage.
6. Per bank. V_{CCIO} = 2.5 V. Does not include pull-up/pull-down.

BLVDS

The MachXO2 family supports the BLVDS standard through emulation. The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs. The input standard is supported by the LVDS differential input buffer. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3-2 is one possible solution for bi-directional multi-point differential signals.

Figure 3-2. BLVDS Multi-point Output Example

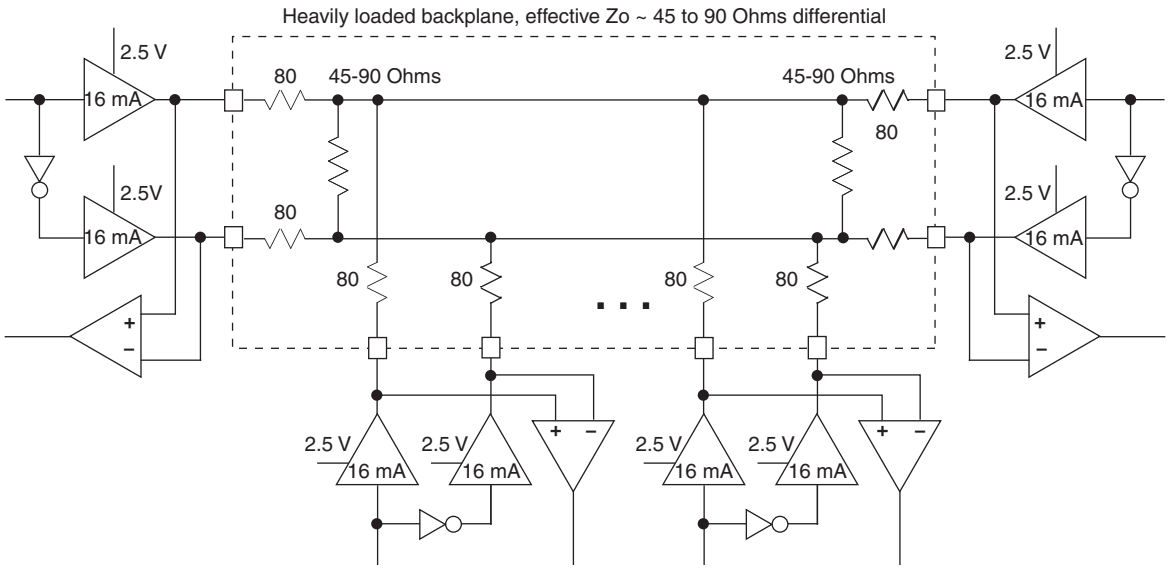


Table 3-2. BLVDS DC Conditions[1]

Over Recommended Operating Conditions

Symbol	Description	Nominal		Units
		Zo = 45	Zo = 90	
Z_{OUT}	Output impedance	20	20	Ohms
R_S	Driver series resistance	80	80	Ohms
R_{TLEFT}	Left end termination	45	90	Ohms
R_{TRIGHT}	Right end termination	45	90	Ohms
V_{OH}	Output high voltage	1.376	1.480	V
V_{OL}	Output low voltage	1.124	1.020	V
V_{OD}	Output differential voltage	0.253	0.459	V
V_{CM}	Output common mode voltage	1.250	1.250	V
I_{DC}	DC output current	11.236	10.204	mA

1. For input buffer, see LVDS table.

MachXO2 External Switching Characteristics – HC/HE Devices[1, 2, 3, 4, 5, 6, 7]

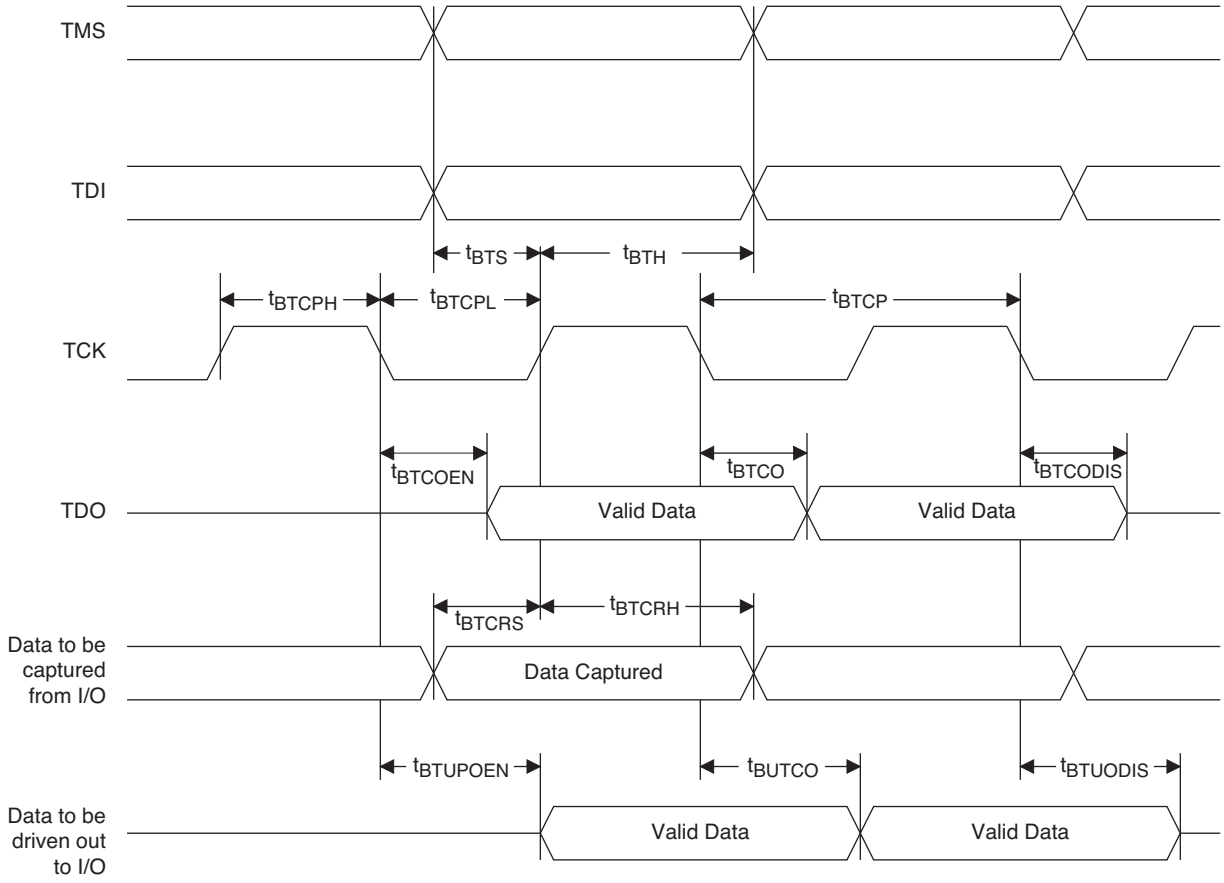
Over Recommended Operating Conditions

Parameter	Description	Device	–6		–5		–4		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Clocks									
Primary Clocks									
f_{MAX_PRI}[8]	Frequency for Primary Clock Tree	All MachXO2 devices	—	388	—	323	—	269	MHz
t_{W_PRI}	Clock Pulse Width for Primary Clock	All MachXO2 devices	0.5	—	0.6	—	0.7	—	ns
t_{SKEW_PRI}	Primary Clock Skew Within a Device	MachXO2-256HC-HE	—	912	—	939	—	975	ps
		MachXO2-640HC-HE	—	844	—	871	—	908	ps
		MachXO2-1200HC-HE	—	868	—	902	—	951	ps
		MachXO2-2000HC-HE	—	867	—	897	—	941	ps
		MachXO2-4000HC-HE	—	865	—	892	—	931	ps
		MachXO2-7000HC-HE	—	902	—	942	—	989	ps
Edge Clock									
f_{MAX_EDGE}[8]	Frequency for Edge Clock	MachXO2-1200 and larger devices	—	400	—	333	—	278	MHz
Pin-LUT-Pin Propagation Delay									
t_{PD}	Best case propagation delay through one LUT-4	All MachXO2 devices	—	6.72	—	6.96	—	7.24	ns
General I/O Pin Parameters (Using Primary Clock without PLL)									
t_{CO}	Clock to Output – PIO Output Register	MachXO2-256HC-HE	—	7.13	—	7.30	—	7.57	ns
		MachXO2-640HC-HE	—	7.15	—	7.30	—	7.57	ns
		MachXO2-1200HC-HE	—	7.44	—	7.64	—	7.94	ns
		MachXO2-2000HC-HE	—	7.46	—	7.66	—	7.96	ns
		MachXO2-4000HC-HE	—	7.51	—	7.71	—	8.01	ns
		MachXO2-7000HC-HE	—	7.54	—	7.75	—	8.06	ns
t_{SU}	Clock to Data Setup – PIO Input Register	MachXO2-256HC-HE	–0.06	—	–0.06	—	–0.06	—	ns
		MachXO2-640HC-HE	–0.06	—	–0.06	—	–0.06	—	ns
		MachXO2-1200HC-HE	–0.17	—	–0.17	—	–0.17	—	ns
		MachXO2-2000HC-HE	–0.20	—	–0.20	—	–0.20	—	ns
		MachXO2-4000HC-HE	–0.23	—	–0.23	—	–0.23	—	ns
		MachXO2-7000HC-HE	–0.23	—	–0.23	—	–0.23	—	ns
t_{H}	Clock to Data Hold – PIO Input Register	MachXO2-256HC-HE	1.75	—	1.95	—	2.16	—	ns
		MachXO2-640HC-HE	1.75	—	1.95	—	2.16	—	ns
		MachXO2-1200HC-HE	1.88	—	2.12	—	2.36	—	ns
		MachXO2-2000HC-HE	1.89	—	2.13	—	2.37	—	ns
		MachXO2-4000HC-HE	1.94	—	2.18	—	2.43	—	ns
		MachXO2-7000HC-HE	1.98	—	2.23	—	2.49	—	ns

Parameter	Description	Device	–6		–5		–4		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
LPDDR[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.369	—	0.395	—	0.421	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.529	—	0.530	—	0.527	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM LPDDR Serial Data Speed		—	280	—	250	—	208	Mbps
f_{SCLK}	SCLK Frequency		—	140	—	125	—	104	MHz
f_{LPDDR}	LPDDR Data Transfer Rate		0	280	0	250	0	208	Mbps
DDR[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.350	—	0.387	—	0.414	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.545	—	0.538	—	0.532	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM DDR Serial Data Speed		—	300	—	250	—	208	Mbps
f_{SCLK}	SCLK Frequency		—	150	—	125	—	104	MHz
f_{MEM_DDR}	MEM DDR Data Transfer Rate		N/A	300	N/A	250	N/A	208	Mbps
DDR2[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.360	—	0.378	—	0.406	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.555	—	0.549	—	0.542	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM DDR Serial Data Speed		—	300	—	250	—	208	Mbps
f_{SCLK}	SCLK Frequency		—	150	—	125	—	104	MHz
f_{MEM_DDR2}	MEM DDR2 Data Transfer Rate		N/A	300	N/A	250	N/A	208	Mbps

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.
2. General I/O timing numbers based on LVCMOS 2.5, 8 mA, 0pf load, fast slew rate.
3. Generic DDR timing numbers based on LVDS I/O (for input, output, and clock ports).
4. DDR timing numbers based on SSTL25. DDR2 timing numbers based on SSTL18. LPDDR timing numbers based in LVCMOS18.
5. 7:1 LVDS (GDDR71) uses the LVDS I/O standard (for input, output, and clock ports).
6. For Generic DDRX1 mode $t_{SU} = t_{HO} = (t_{DVE} - t_{DVA} - 0.03\ ns)/2$.
7. The t_{SU_DEL} and t_{H_DEL} values use the SCLK_ZERHOLD default step size. Each step is 105 ps (–6), 113 ps (–5), 120 ps (–4).
8. This number for general purpose usage. Duty cycle tolerance is +/– 10%.
9. Duty cycle is +/–5% for system usage.
10. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with the device selected.
11. High-speed DDR and LVDS not supported in SG32 (32 QFN) packages.
12. Advance information for MachXO2 devices in 48 QFN packages.
13. DDR memory interface not supported in QN84 (84 QFN) and SG32 (32 QFN) packages.

Figure 3-12. JTAG Port Timing Waveforms



	MachXO2-1200					MachXO2-1200U
	100 TQFP	132 csBGA	144 TQFP	25 WLCSP	32 QFN[1]	256 ftBGA
General Purpose I/O per Bank						
Bank 0	18	25	27	11	9	50
Bank 1	21	26	26	0	2	52
Bank 2	20	28	28	7	9	52
Bank 3	20	25	26	0	2	16
Bank 4	0	0	0	0	0	16
Bank 5	0	0	0	0	0	20
Total General Purpose Single Ended I/O	79	104	107	18	22	206
Differential I/O per Bank						
Bank 0	9	13	14	5	4	25
Bank 1	10	13	13	0	1	26
Bank 2	10	14	14	2	4	26
Bank 3	10	12	13	0	1	8
Bank 4	0	0	0	0	0	8
Bank 5	0	0	0	0	0	10
Total General Purpose Differential I/O	39	52	54	7	10	103
Dual Function I/O	31	33	33	18	22	33
High-speed Differential I/O						
Bank 0	4	7	7	0	0	14
Gearboxes						
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	4	7	7	0	0	14
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	5	7	7	0	2	14
DQS Groups						
Bank 1	1	2	2	0	0	2
VCCIO Pins						
Bank 0	2	3	3	1	2	4
Bank 1	2	3	3	0	1	4
Bank 2	2	3	3	1	2	4
Bank 3	3	3	3	0	1	1
Bank 4	0	0	0	0	0	2
Bank 5	0	0	0	0	0	1
VCC	2	4	4	2	2	8
GND	8	10	12	2	2	24
NC	1	1	8	0	0	1
Reserved for Configuration	1	1	1	1	1	1
Total Count of Bonded Pins	100	132	144	25	32	256

1. Lattice recommends soldering the central thermal pad onto the top PCB ground for improved thermal resistance.

	MachXO2-7000					
	144 TQFP	**256 caBGA**	**256 ftBGA**	**332 caBGA**	**400 caBGA**	**484 fpBGA**
General Purpose I/O per Bank						
Bank 0	27	50	50	68	83	82
Bank 1	29	52	52	70	84	84
Bank 2	29	52	52	70	84	84
Bank 3	9	16	16	24	28	28
Bank 4	10	16	16	16	24	24
Bank 5	10	20	20	30	32	32
Total General Purpose Single Ended I/O	114	206	206	278	335	334
Differential I/O per Bank						
Bank 0	14	25	25	34	42	41
Bank 1	14	26	26	35	42	42
Bank 2	14	26	26	35	42	42
Bank 3	4	8	8	12	14	14
Bank 4	5	8	8	8	12	12
Bank 5	5	10	10	15	16	16
Total General Purpose Differential I/O	56	103	103	139	168	167
Dual Function I/O	37	37	37	37	37	37
High-speed Differential I/O						
Bank 0	9	20	20	21	21	21
Gearboxes						
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	9	20	20	21	21	21
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	14	20	20	21	21	21
DQS Groups						
Bank 1	2	2	2	2	2	2
VCCIO Pins						
Bank 0	3	4	4	4	5	10
Bank 1	3	4	4	4	5	10
Bank 2	3	4	4	4	5	10
Bank 3	1	1	1	2	2	3
Bank 4	1	2	2	1	2	4
Bank 5	1	1	1	2	2	3
VCC	4	8	8	8	10	12
GND	12	24	24	27	33	48
NC	1	1	1	1	0	49
Reserved for Configuration	1	1	1	1	1	1
Total Count of Bonded Pins	144	256	256	332	400	484

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-7000ZE-1TG144C	6864	1.2 V	–1	Halogen-Free TQFP	144	COM
LCMXO2-7000ZE-2TG144C	6864	1.2 V	–2	Halogen-Free TQFP	144	COM
LCMXO2-7000ZE-3TG144C	6864	1.2 V	–3	Halogen-Free TQFP	144	COM
LCMXO2-7000ZE-1BG256C	6864	1.2 V	–1	Halogen-Free caBGA	256	COM
LCMXO2-7000ZE-2BG256C	6864	1.2 V	–2	Halogen-Free caBGA	256	COM
LCMXO2-7000ZE-3BG256C	6864	1.2 V	–3	Halogen-Free caBGA	256	COM
LCMXO2-7000ZE-1FTG256C	6864	1.2 V	–1	Halogen-Free ftBGA	256	COM
LCMXO2-7000ZE-2FTG256C	6864	1.2 V	–2	Halogen-Free ftBGA	256	COM
LCMXO2-7000ZE-3FTG256C	6864	1.2 V	–3	Halogen-Free ftBGA	256	COM
LCMXO2-7000ZE-1BG332C	6864	1.2 V	–1	Halogen-Free caBGA	332	COM
LCMXO2-7000ZE-2BG332C	6864	1.2 V	–2	Halogen-Free caBGA	332	COM
LCMXO2-7000ZE-3BG332C	6864	1.2 V	–3	Halogen-Free caBGA	332	COM
LCMXO2-7000ZE-1FG484C	6864	1.2 V	–1	Halogen-Free fpBGA	484	COM
LCMXO2-7000ZE-2FG484C	6864	1.2 V	–2	Halogen-Free fpBGA	484	COM
LCMXO2-7000ZE-3FG484C	6864	1.2 V	–3	Halogen-Free fpBGA	484	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200ZE-1TG100CR1[1]	1280	1.2 V	–1	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-2TG100CR1[1]	1280	1.2 V	–2	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-3TG100CR1[1]	1280	1.2 V	–3	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-1MG132CR1[1]	1280	1.2 V	–1	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-2MG132CR1[1]	1280	1.2 V	–2	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-3MG132CR1[1]	1280	1.2 V	–3	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-1TG144CR1[1]	1280	1.2 V	–1	Halogen-Free TQFP	144	COM
LCMXO2-1200ZE-2TG144CR1[1]	1280	1.2 V	–2	Halogen-Free TQFP	144	COM
LCMXO2-1200ZE-3TG144CR1[1]	1280	1.2 V	–3	Halogen-Free TQFP	144	COM

1. Specifications for the “LCMXO2-1200ZE-speed package CR1” are the same as the “LCMXO2-1200ZE-speed package C” devices respectively, except as specified in the R1 Device Specifications section of this data sheet.

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000UHC-4FG484C	2112	2.5 V / 3.3 V	–4	Halogen-Free fpBGA	484	COM
LCMXO2-2000UHC-5FG484C	2112	2.5 V / 3.3 V	–5	Halogen-Free fpBGA	484	COM
LCMXO2-2000UHC-6FG484C	2112	2.5 V / 3.3 V	–6	Halogen-Free fpBGA	484	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-4000HC-4QN84C	4320	2.5 V / 3.3 V	–4	Halogen-Free QFN	84	COM
LCMXO2-4000HC-5QN84C	4320	2.5 V / 3.3 V	–5	Halogen-Free QFN	84	COM
LCMXO2-4000HC-6QN84C	4320	2.5 V / 3.3 V	–6	Halogen-Free QFN	84	COM
LCMXO2-4000HC-4MG132C	4320	2.5 V / 3.3 V	–4	Halogen-Free csBGA	132	COM
LCMXO2-4000HC-5MG132C	4320	2.5 V / 3.3 V	–5	Halogen-Free csBGA	132	COM
LCMXO2-4000HC-6MG132C	4320	2.5 V / 3.3 V	–6	Halogen-Free csBGA	132	COM
LCMXO2-4000HC-4TG144C	4320	2.5 V / 3.3 V	–4	Halogen-Free TQFP	144	COM
LCMXO2-4000HC-5TG144C	4320	2.5 V / 3.3 V	–5	Halogen-Free TQFP	144	COM
LCMXO2-4000HC-6TG144C	4320	2.5 V / 3.3 V	–6	Halogen-Free TQFP	144	COM
LCMXO2-4000HC-4BG256C	4320	2.5 V / 3.3 V	–4	Halogen-Free caBGA	256	COM
LCMXO2-4000HC-5BG256C	4320	2.5 V / 3.3 V	–5	Halogen-Free caBGA	256	COM
LCMXO2-4000HC-6BG256C	4320	2.5 V / 3.3 V	–6	Halogen-Free caBGA	256	COM
LCMXO2-4000HC-4FTG256C	4320	2.5 V / 3.3 V	–4	Halogen-Free ftBGA	256	COM
LCMXO2-4000HC-5FTG256C	4320	2.5 V / 3.3 V	–5	Halogen-Free ftBGA	256	COM
LCMXO2-4000HC-6FTG256C	4320	2.5 V / 3.3 V	–6	Halogen-Free ftBGA	256	COM
LCMXO2-4000HC-4BG332C	4320	2.5 V / 3.3 V	–4	Halogen-Free caBGA	332	COM
LCMXO2-4000HC-5BG332C	4320	2.5 V / 3.3 V	–5	Halogen-Free caBGA	332	COM
LCMXO2-4000HC-6BG332C	4320	2.5 V / 3.3 V	–6	Halogen-Free caBGA	332	COM
LCMXO2-4000HC-4FG484C	4320	2.5 V / 3.3 V	–4	Halogen-Free fpBGA	484	COM
LCMXO2-4000HC-5FG484C	4320	2.5 V / 3.3 V	–5	Halogen-Free fpBGA	484	COM
LCMXO2-4000HC-6FG484C	4320	2.5 V / 3.3 V	–6	Halogen-Free fpBGA	484	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-7000HC-4TG144C	6864	2.5 V / 3.3 V	–4	Halogen-Free TQFP	144	COM
LCMXO2-7000HC-5TG144C	6864	2.5 V / 3.3 V	–5	Halogen-Free TQFP	144	COM
LCMXO2-7000HC-6TG144C	6864	2.5 V / 3.3 V	–6	Halogen-Free TQFP	144	COM
LCMXO2-7000HC-4BG256C	6864	2.5 V / 3.3 V	–4	Halogen-Free caBGA	256	COM
LCMXO2-7000HC-5BG256C	6864	2.5 V / 3.3 V	–5	Halogen-Free caBGA	256	COM
LCMXO2-7000HC-6BG256C	6864	2.5 V / 3.3 V	–6	Halogen-Free caBGA	256	COM
LCMXO2-7000HC-4FTG256C	6864	2.5 V / 3.3 V	–4	Halogen-Free ftBGA	256	COM
LCMXO2-7000HC-5FTG256C	6864	2.5 V / 3.3 V	–5	Halogen-Free ftBGA	256	COM
LCMXO2-7000HC-6FTG256C	6864	2.5 V / 3.3 V	–6	Halogen-Free ftBGA	256	COM
LCMXO2-7000HC-4BG332C	6864	2.5 V / 3.3 V	–4	Halogen-Free caBGA	332	COM
LCMXO2-7000HC-5BG332C	6864	2.5 V / 3.3 V	–5	Halogen-Free caBGA	332	COM
LCMXO2-7000HC-6BG332C	6864	2.5 V / 3.3 V	–6	Halogen-Free caBGA	332	COM
LCMXO2-7000HC-4FG400C	6864	2.5 V / 3.3 V	–4	Halogen-Free fpBGA	400	COM
LCMXO2-7000HC-5FG400C	6864	2.5 V / 3.3 V	–5	Halogen-Free fpBGA	400	COM
LCMXO2-7000HC-6FG400C	6864	2.5 V / 3.3 V	–6	Halogen-Free fpBGA	400	COM
LCMXO2-7000HC-4FG484C	6864	2.5 V / 3.3 V	–4	Halogen-Free fpBGA	484	COM
LCMXO2-7000HC-5FG484C	6864	2.5 V / 3.3 V	–5	Halogen-Free fpBGA	484	COM
LCMXO2-7000HC-6FG484C	6864	2.5 V / 3.3 V	–6	Halogen-Free fpBGA	484	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200HC-4TG100CR1[1]	1280	2.5 V / 3.3 V	–4	Halogen-Free TQFP	100	COM
LCMXO2-1200HC-5TG100CR1[1]	1280	2.5 V / 3.3 V	–5	Halogen-Free TQFP	100	COM
LCMXO2-1200HC-6TG100CR1[1]	1280	2.5 V / 3.3 V	–6	Halogen-Free TQFP	100	COM
LCMXO2-1200HC-4MG132CR1[1]	1280	2.5 V / 3.3 V	–4	Halogen-Free csBGA	132	COM
LCMXO2-1200HC-5MG132CR1[1]	1280	2.5 V / 3.3 V	–5	Halogen-Free csBGA	132	COM
LCMXO2-1200HC-6MG132CR1[1]	1280	2.5 V / 3.3 V	–6	Halogen-Free csBGA	132	COM
LCMXO2-1200HC-4TG144CR1[1]	1280	2.5 V / 3.3 V	–4	Halogen-Free TQFP	144	COM
LCMXO2-1200HC-5TG144CR1[1]	1280	2.5 V / 3.3 V	–5	Halogen-Free TQFP	144	COM
LCMXO2-1200HC-6TG144CR1[1]	1280	2.5 V / 3.3 V	–6	Halogen-Free TQFP	144	COM

1. Specifications for the “LCMXO2-1200HC-speed package CR1” are the same as the “LCMXO2-1200HC-speed package C” devices respectively, except as specified in the R1 Device Specifications section of this data sheet.

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200HC-4TG100IR1[1]	1280	2.5 V / 3.3 V	–4	Halogen-Free TQFP	100	IND
LCMXO2-1200HC-5TG100IR1[1]	1280	2.5 V / 3.3 V	–5	Halogen-Free TQFP	100	IND
LCMXO2-1200HC-6TG100IR1[1]	1280	2.5 V / 3.3 V	–6	Halogen-Free TQFP	100	IND
LCMXO2-1200HC-4MG132IR1[1]	1280	2.5 V / 3.3 V	–4	Halogen-Free csBGA	132	IND
LCMXO2-1200HC-5MG132IR1[1]	1280	2.5 V / 3.3 V	–5	Halogen-Free csBGA	132	IND
LCMXO2-1200HC-6MG132IR1[1]	1280	2.5 V / 3.3 V	–6	Halogen-Free csBGA	132	IND
LCMXO2-1200HC-4TG144IR1[1]	1280	2.5 V / 3.3 V	–4	Halogen-Free TQFP	144	IND
LCMXO2-1200HC-5TG144IR1[1]	1280	2.5 V / 3.3 V	–5	Halogen-Free TQFP	144	IND
LCMXO2-1200HC-6TG144IR1[1]	1280	2.5 V / 3.3 V	–6	Halogen-Free TQFP	144	IND

1. Specifications for the “LCMXO2-1200HC-speed package IR1” are the same as the “LCMXO2-1200ZE-speed package I” devices respectively, except as specified in the R1 Device Specifications section of this data sheet.